

SKUT 115/12 V2



SEMIPONT® 5

Three phase antiparallel thyristor module

SKUT 115/12 V2

Features

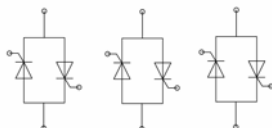
- Compact design
- Two screws mounting
- Heat transfer and isolation through direct copper board (Low R_{th})
- Low resistance in steady-state and high reliability
- High surge currents
- Glass passivated thyristor chips
- UL recognized, file no. E 63 532

Typical Applications*

- Soft starter
- Light control (e.g. studios, theaters)
- Temperature control (e.g. oven, chemical processes)

Remarks

- $I_{RMS}=105A$, for W3C application, sin.180° and $T_S=85^{\circ}C$



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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Chip				
I _{T(AV)}	sinus 180°	T _s = 25 °C	127	A
		T _s = 85 °C	71	A
I _{TSM}	10 ms	T _j = 25 °C	1500	A
		T _j = 130 °C	1250	A
i ² t	10 ms	T _j = 25 °C	11250	A ² s
		T _j = 130 °C	7813	A ² s
V _{RSM}			1300	V
V _{RRM}			1200	V
V _{DRM}			1200	V
(di/dt) _{cr}	T _j = 130 °C		50	A/μs
(dv/dt) _{cr}	T _j = 130 °C		500	V/μs
T _j			-40 ... 125	°C
Module				
T _{stg}			-40 ... 125	°C
V _{isol}	ac; 50Hz; r.m.s	1 min	3000	V
		1 s	3600	V

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Chip						
V _T	T _j = 25 °C, I _T = 150 A				1.6	V
V _{T(TO)}	T _j = 130 °C				0.9	V
r _T	T _j = 130 °C				5.00	mΩ
I _{DD} ;I _{RD}	T _j = 130 °C, V _{RD} =V _{RRM}				20	mA
t _{gd}	T _j = 25 °C, I _G = 1 A, di _G /dt = 1 A/μs			1		μs
t _{gr}	V _D = 0.67 * V _{DRM}			2		μs
t _q	T _j = 130 °C			150		μs
I _H	T _j = 25 °C				200	mA
I _L	T _j = 25 °C, R _G = 33 Ω				600	mA
V _{GT}	T _j = 25 °C, d.c.		3			V
I _{GT}	T _j = 25 °C, d.c.		150			mA
V _{GD}	T _j = 130 °C, d.c.				0.25	V
I _{GD}	T _j = 115 °C, d.c.		6			mA
R _{th(j-s)}	continuous DC	per thyristor				K/W
R _{th(j-s)}		per module				K/W
R _{th(j-s)}	sin. 180°	per thyristor				K/W
R _{th(j-s)}		per module	0.32			K/W
R _{th(j-s)}	rec. 120°	per thyristor				K/W
R _{th(j-s)}		per module				K/W
Module						
R _{th(c-s)}						K/W
						K/W
M _s	to heatsink		2.25		2.5	Nm
M _t						Nm
a						m/s ²
w			75			g

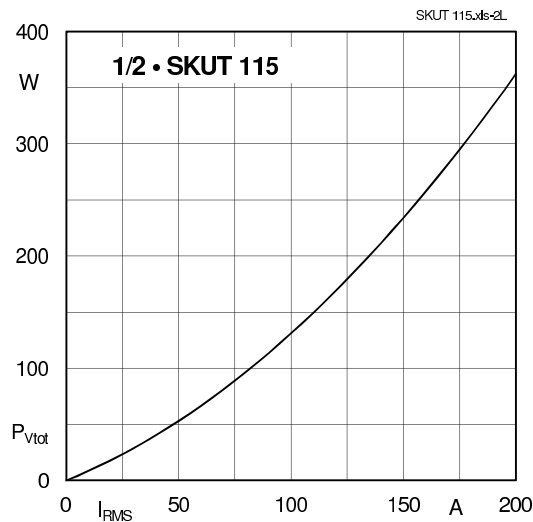


Fig. 2: Power dissipation per thyristor vs r.m.s. current

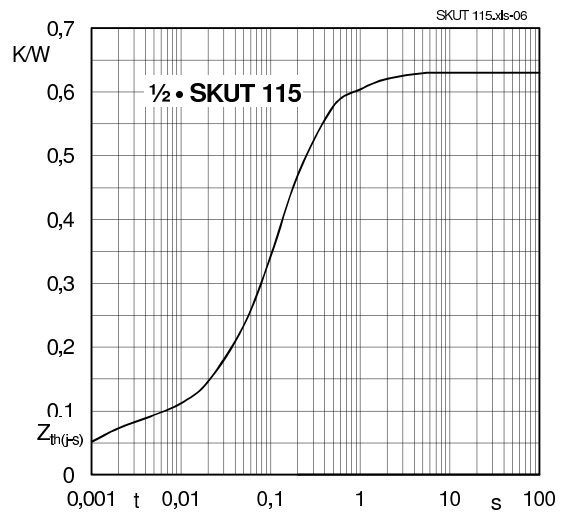


Fig. 6: Transient thermal impedance $Z_{th}(j-s)$

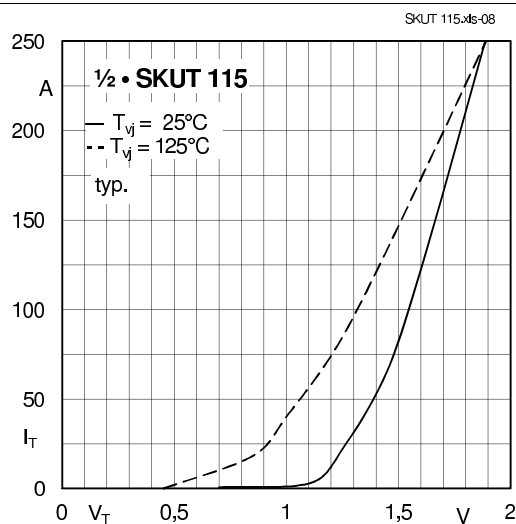


Fig. 8: On state characteristics

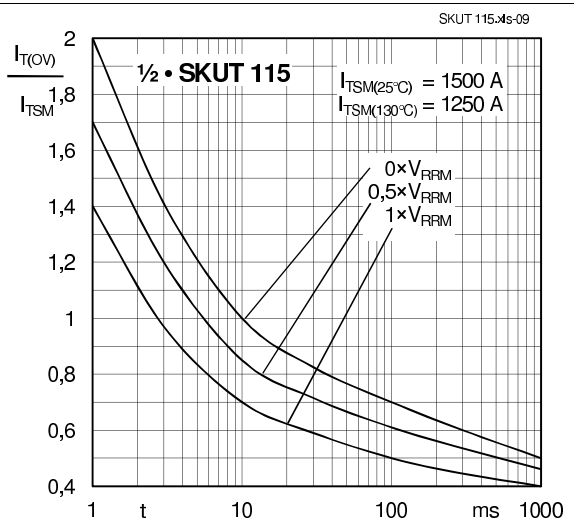


Fig. 9: Surge overload current vs. time

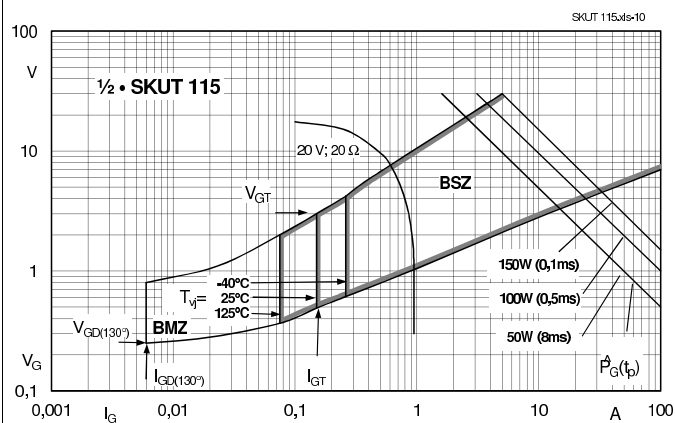
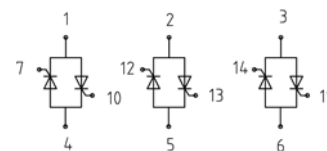
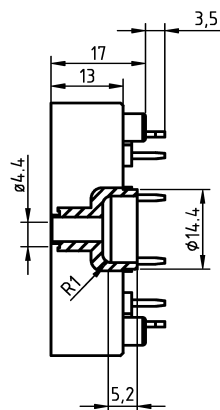
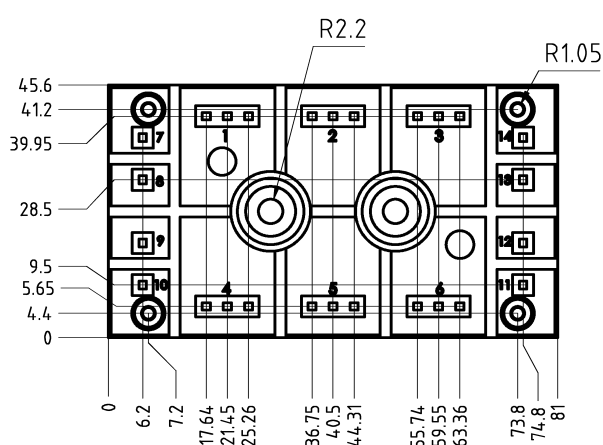
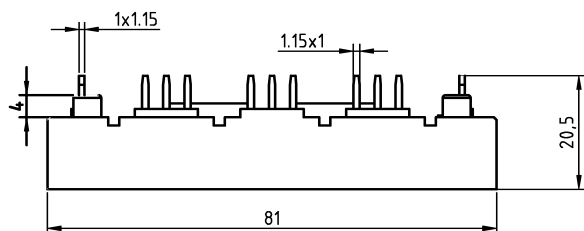


Fig. 10: Gate trigger characteristic



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.